

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = 25^\circ\text{C}$
-20V	54m Ω @ $V_{GS} = -4.5\text{V}$	-2.5A
	90m Ω @ $V_{GS} = -1.8\text{V}$	-1.8A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

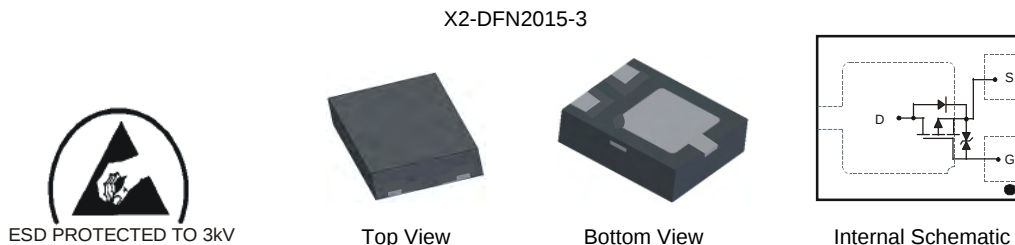
- Backlighting
- Power Management Functions
- DC-DC Converters
-

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device, Halogen and Antimony Free (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

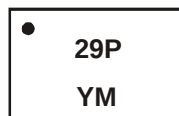


Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2069UFY4-7	X2-DFN2015-3	3000/Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



29P = Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 4)	Steady State	T _A = 25°C T _A = 70°C	I _D	-2.5 -2.2	A
Pulsed Drain Current (Note 5)			I _{DM}	-12	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	0.53	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{θJA}	231	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.3	-0.55	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	36	54	mΩ	V _{GS} = -4.5V, I _D = -2.5A
			46	69		V _{GS} = -2.5V, I _D = -2.2A
			60	90		V _{GS} = -1.8V, I _D = -2.0A
Forward Transfer Admittance	Y _{fs}	—	8	—	S	V _{DS} = -5V, I _D = -2.5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	214	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	104	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	25	—	pF	
Gate Resistance	R _g	—	250	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 7)						
Total Gate Charge	Q _g	—	9.1	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A
Gate-Source Charge	Q _{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.7	—	nC	
Turn-On Delay Time	t _{D(on)}	—	80.4	160	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _D = 2.5Ω, R _G = 3.0Ω
Turn-On Rise Time	t _r	—	155.1	210	ns	
Turn-Off Delay Time	t _{D(off)}	—	688.1	1376	ns	
Turn-Off Fall Time	t _f	—	423.8	848	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

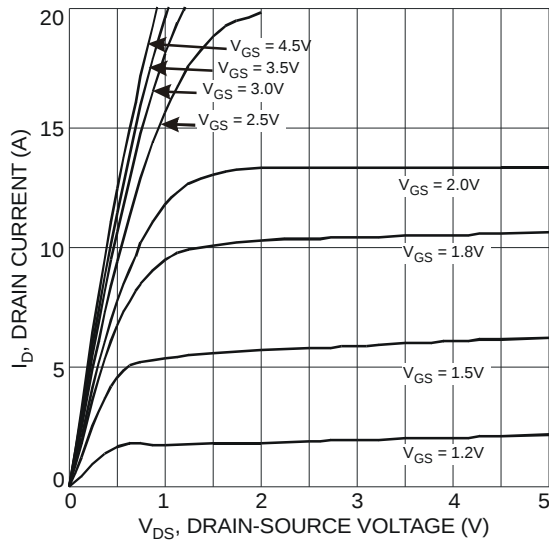


Fig. 1 Typical Output Characteristic

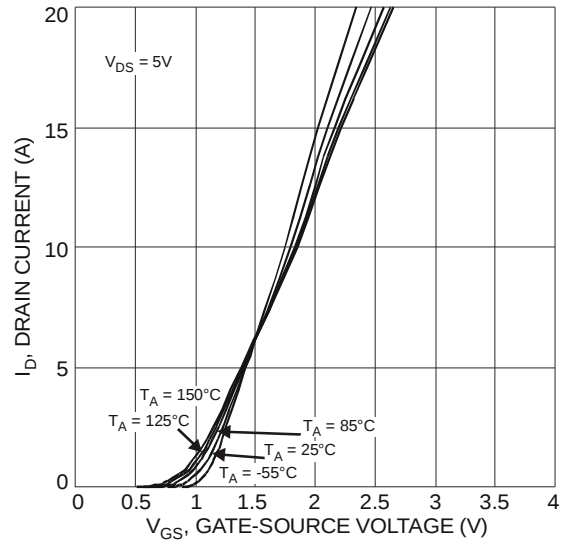


Fig. 2 Typical Transfer Characteristic

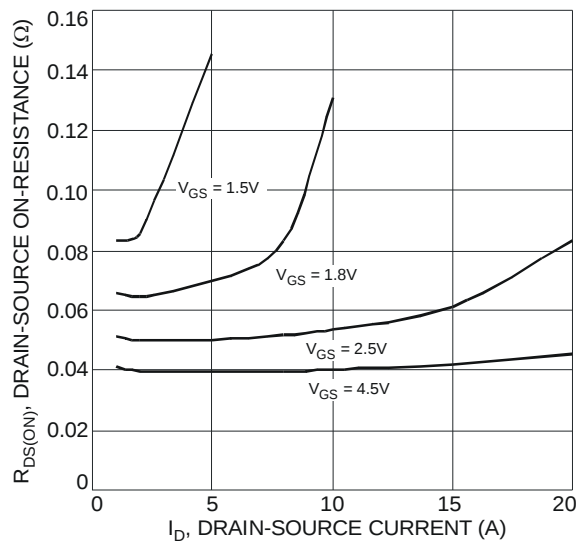


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

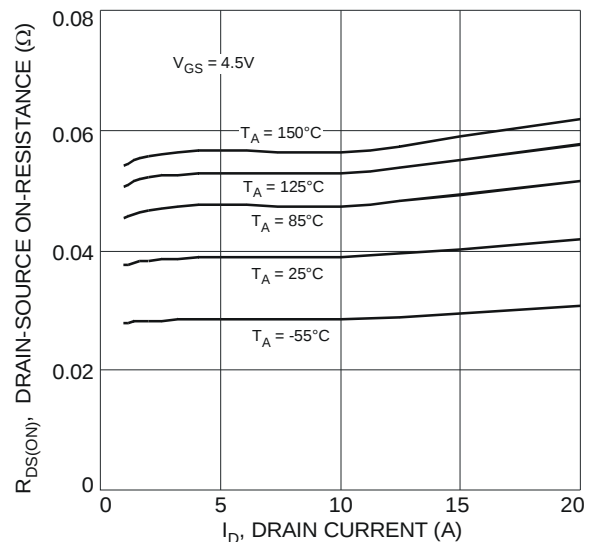


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

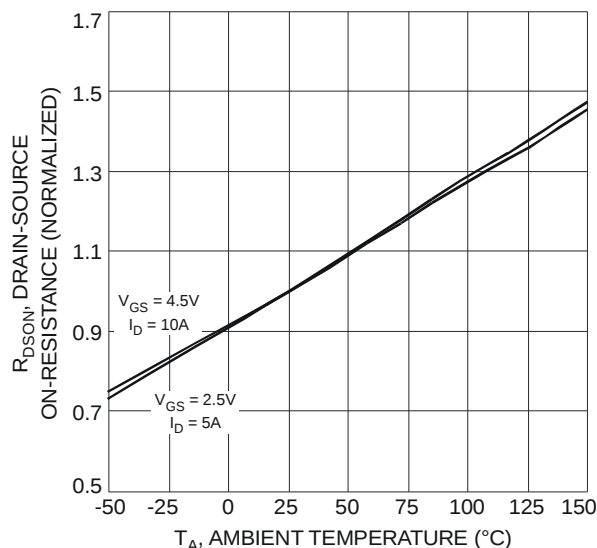


Fig. 5 On-Resistance Variation with Temperature

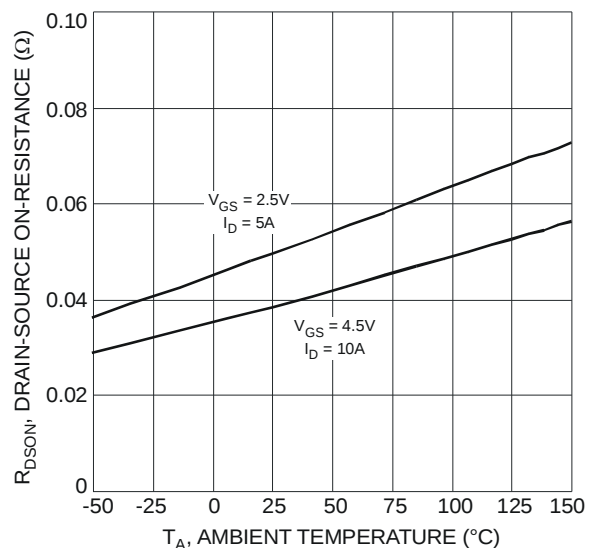


Fig. 6 On-Resistance Variation with Temperature

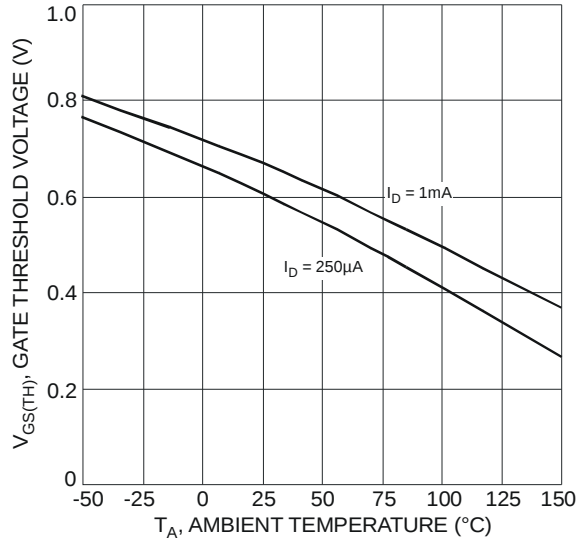


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

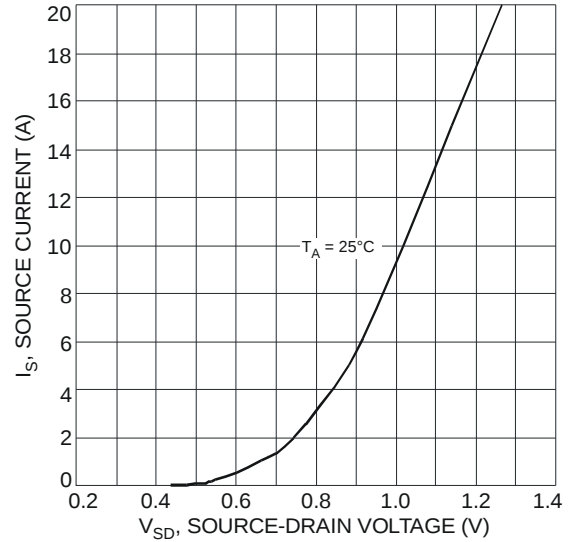


Fig. 8 Diode Forward Voltage vs. Current

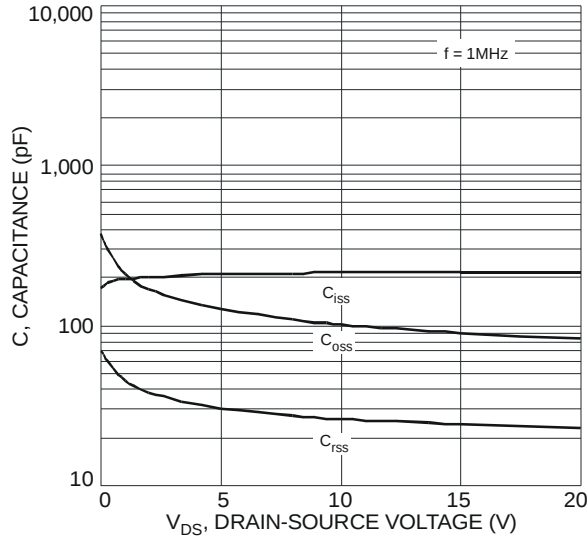


Fig. 9 Typical Capacitance

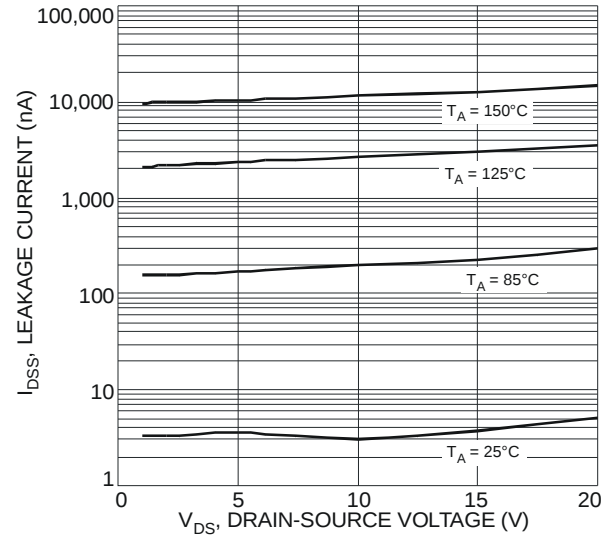


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

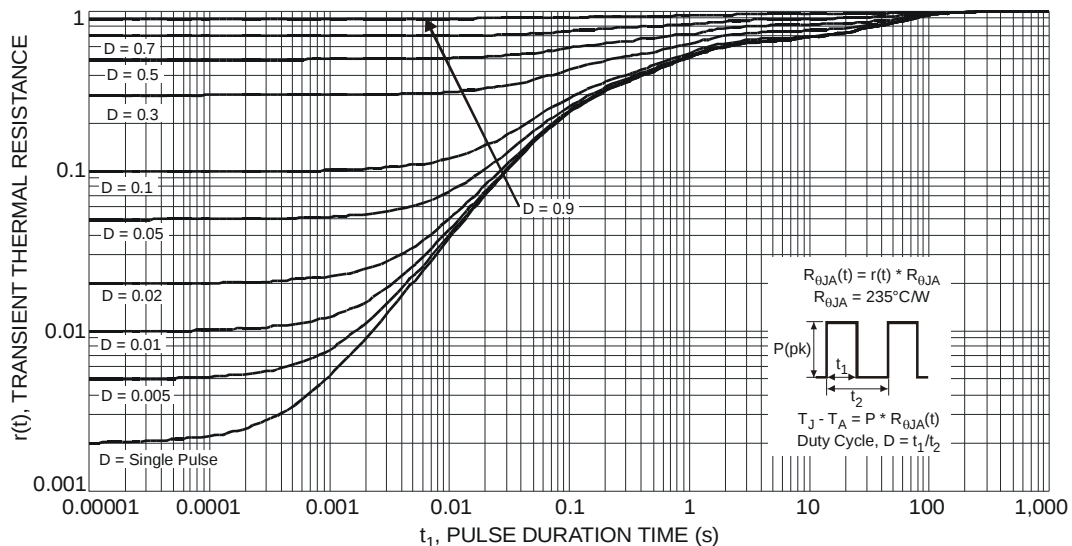
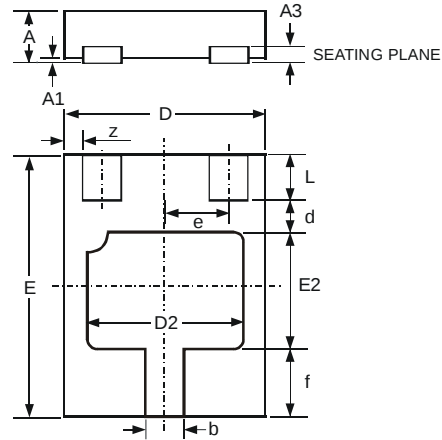


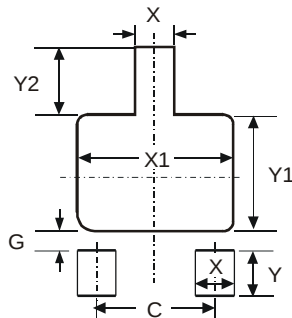
Fig. 11 Transient Thermal Response

Package Outline Dimensions



X2-DFN2015-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
d	—	—	0.30
D	1.45	1.575	1.50
D2	1.00	1.20	1.10
e	—	—	0.50
E	1.95	2.075	2.00
E2	0.70	0.90	0.80
f	—	—	0.60
L	0.25	0.35	0.30
z	—	—	0.125
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	1.00
G	0.15
X	0.31
X1	1.30
Y	0.50
Y1	1.00
Y2	0.65

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